

- B1
Concl'd
Sub
Concl'd*
2. (Twice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,
wherein the channel forming region has a convex portion or a concave portion extending in a channel width direction, and
wherein zero or one grain boundary is contained in the channel forming region.
3. (Twice Amended) A semiconductor device comprising a TFT containing an active layer having a channel forming region,
wherein the channel forming region has a convex portion or a concave portion extending in a channel width direction, and
wherein the number of grain boundaries crossing the channel forming region in the width direction of the channel is zero or one.

- B2
Sub
C2*
11. (Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,
wherein said channel forming region has at least one convex portion extending in a direction perpendicular to a channel length direction.
12. (Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,
wherein said channel forming region has at least one concave portion extending in a direction perpendicular to a channel length direction.

- B&C conc'd
S&S C conc'd*
13. (Amended) A semiconductor device comprising:
a semiconductor layer formed over substrate; and
a channel forming region and source and drain regions formed in said semiconductor
layer,
wherein said channel forming region has at least one convex portion extending in a
channel width direction.
14. (Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor
layer,
wherein said channel forming region has at least one concave portion extending in a
channel width direction.
15. (Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor
layer,
wherein said channel forming region has at least one convex portion extending in a
direction perpendicular to a carrier flow direction.
16. (Amended) A semiconductor device comprising:
a semiconductor layer formed over a substrate;
a channel forming region and source and drain regions formed in said semiconductor
layer; and
wherein said channel forming region has at least one concave portion extending in a
direction perpendicular to a carrier flow direction.